

ABSTRACT

A semiconductor device includes a substrate including an active pattern, a channel pattern on the active pattern and including semiconductor patterns vertically stacked and spaced apart from each other, a source/drain pattern connected to the semiconductor patterns, a gate electrode on the semiconductor patterns and extending in a first direction, and a gate insulating layer between the semiconductor patterns and the gate electrode. A first semiconductor pattern of the semiconductor patterns includes opposite side surfaces in the first direction, and bottom and top surfaces. The gate insulating layer covers the opposite side surfaces, and the bottom and top surfaces and includes a first region on one of the opposite side surfaces of the first semiconductor pattern and a second region on one of the top or bottom surfaces of the first semiconductor pattern, and a thickness of the first region may be greater than a thickness of the second region.

FIG. 6B